



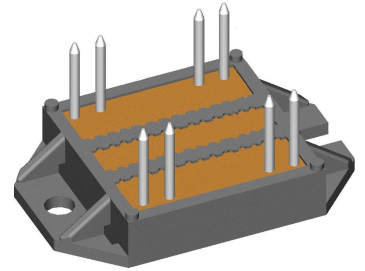
# FRED Module

$V_{RRM} = 1200\text{ V}$   
 $I_{FAV} = 2 \times 60\text{ A}$   
 $t_{rr} = 50\text{ ns}$

Fast Recovery Epitaxial Diode  
 Low Loss and Soft Recovery  
 Parallel legs

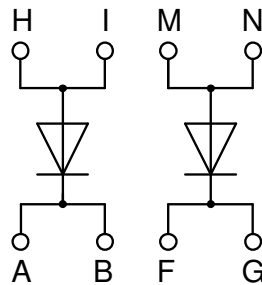
Part number

**DSEI2x61-12P**



Backside: isolated

E72873



### Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

### Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

### Package: ECO-PAC1

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 9 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Disclaimer Notice

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Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$I_R$	reverse current, drain current	$V_R = 1200 V$	$T_{VJ} = 25^{\circ}C$		2.2	mA	
		$V_R = 960 V$	$T_{VJ} = 125^{\circ}C$		14	mA	
$V_F$	forward voltage drop	$I_F = 60 A$	$T_{VJ} = 25^{\circ}C$		2.41	V	
		$I_F = 120 A$			2.76	V	
		$I_F = 60 A$	$T_{VJ} = 150^{\circ}C$		2.05	V	
		$I_F = 120 A$			2.56	V	
$I_{FAV}$	average forward current	$T_C = 45^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$		60	A	
$V_{FO}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.58	V	
$r_F$	slope resistance				7.9	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				0.7	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.10		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		180	W	
$I_{FSM}$	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		450	A	
$C_J$	junction capacitance	$V_R = 600 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		31	pF	
$I_{RM}$	max. reverse recovery current	} $I_F = 60 A; V_R = 540 V$ $-di_F/dt = 300 A/\mu s$	$T_{VJ} = 25^{\circ}C$		13	A	
			$T_{VJ} = 100^{\circ}C$		20	A	
$t_{rr}$	reverse recovery time		$T_{VJ} = 25^{\circ}C$		190	ns	
			$T_{VJ} = 100^{\circ}C$		380	ns	



Package ECO-PAC1		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			100	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				19		g
$M_D$	mounting torque		1.4		2	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	10.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI2x61-12P	DSEI2x61-12P	Box	25	490806

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^{\circ}C$

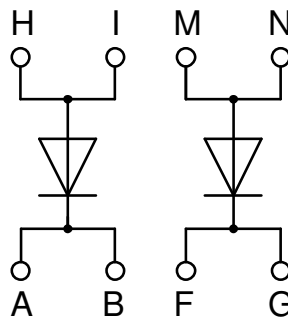
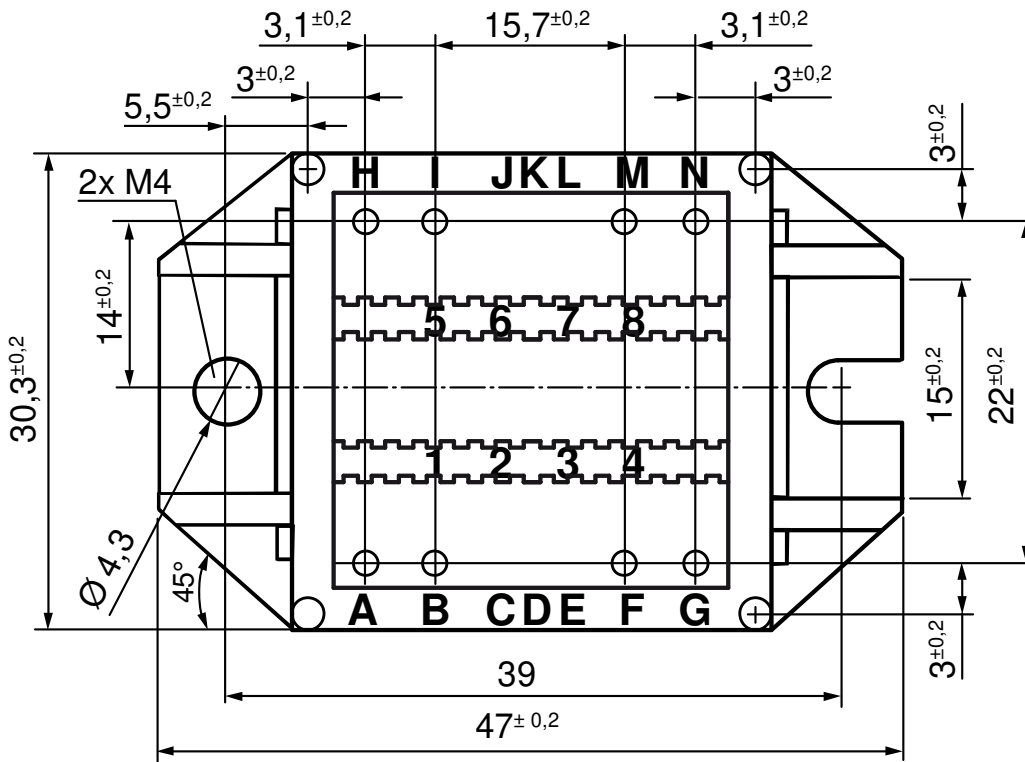
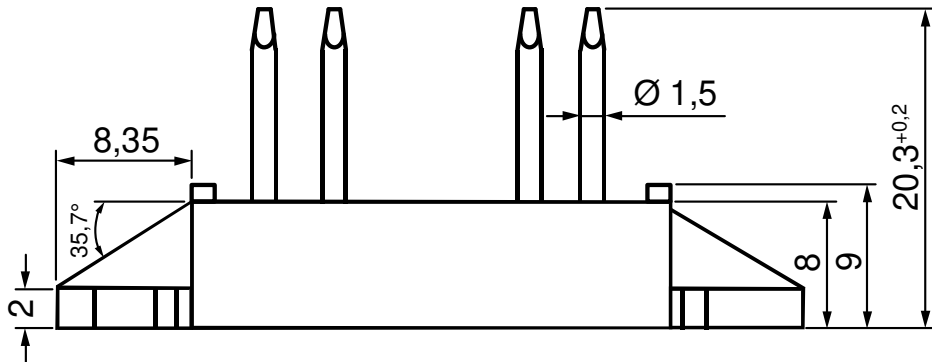


**Fast Diode**

$V_{0\ max}$	threshold voltage	1.58	V
$R_{0\ max}$	slope resistance *	6.6	mΩ



Outlines ECO-PAC1





**Fast Diode**

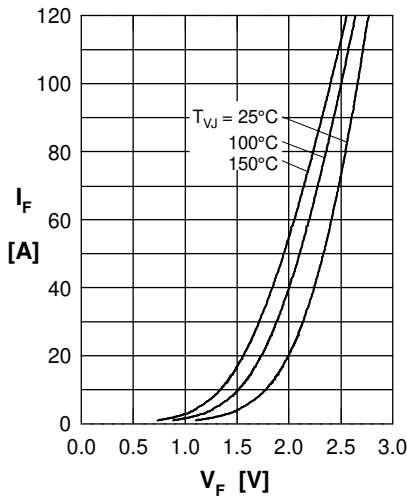


Fig. 1 Forward current  $I_F$  versus max. forward voltage drop  $V_F$

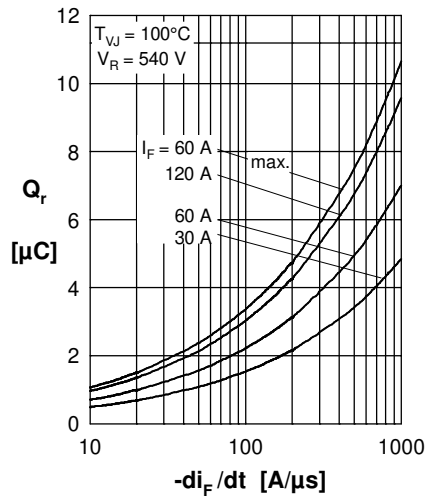


Fig. 2 Typ. reverse recov. charge  $Q_r$  versus  $-di_F/dt$

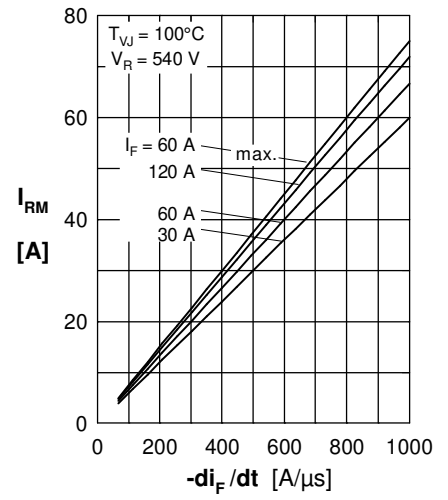


Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$

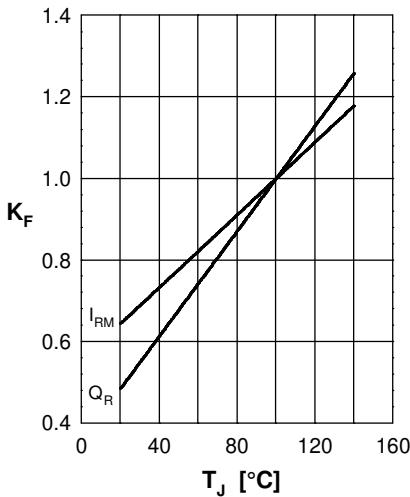


Fig. 4 Dynamic parameters  $Q_r, I_{RM}$  versus  $T_{VJ}$

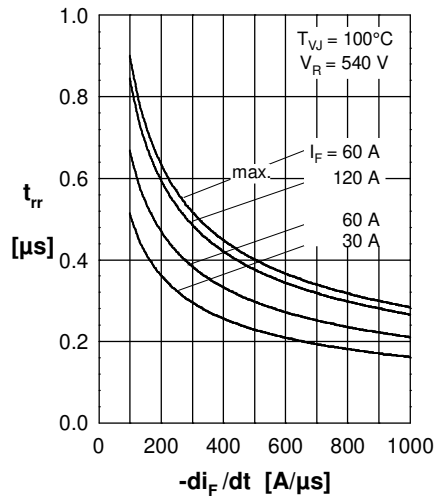


Fig. 5 Typ. recovery time  $t_{rr}$  versus  $-di_F/dt$

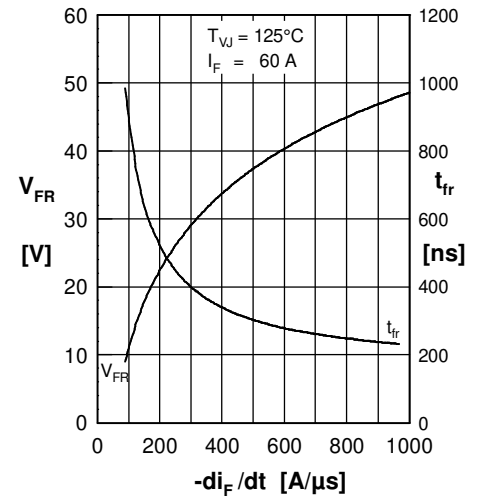


Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$

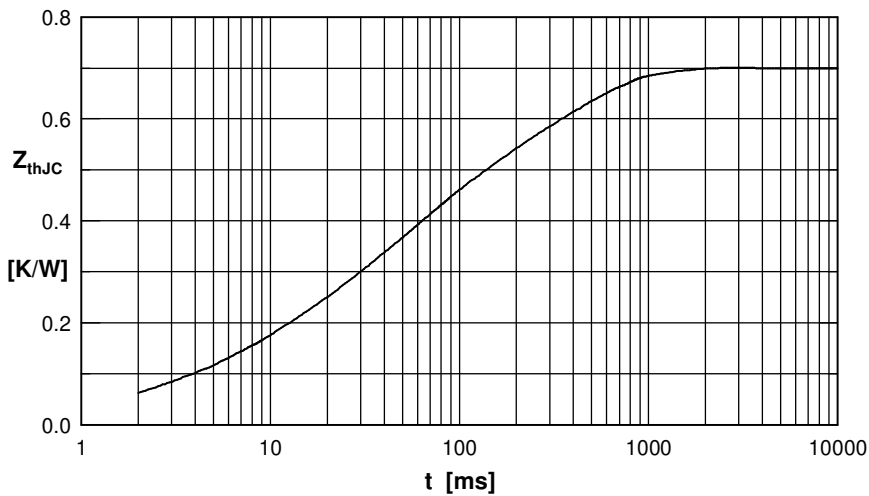


Fig. 7 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.120	0.0100
2	0.045	0.0020
3	0.105	0.0500
4	0.160	0.0500
5	0.270	0.3500